

1. Record Nr.	UNINA9911020362203321
Titolo	Charge transport in disordered solids with applications in electronics / / edited by Sergei Baranovski
Pubbl/distr/stampa	Hoboken, NJ, : Wiley, c2006
ISBN	9786610649464 9781280649462 1280649461 9780470095065 0470095067 9780470095058 0470095059
Descrizione fisica	1 online resource (499 p.)
Collana	Wiley series in materials for electronic and optoelectronic applications
Altri autori (Persone)	BaranovskiSergei
Disciplina	621.3815/2
Soggetti	Amorphous semiconductors - Electric properties Solids - Electric properties Semiconductors - Materials
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Cover; Contents; Series Preface; Preface; 1: Charge Transport via Delocalized States in Disordered Materials; 1.1 INTRODUCTION; 1.2 TRANSPORT BY ELECTRONS IN EXTENDED STATES FAR FROM THE MOBILITY EDGES; 1.2.1 Weak-scattering theories; 1.2.2 Weak localization; 1.2.3 Interaction effects; 1.3 SCALING THEORY OF LOCALIZATION; 1.3.1 Main ideas of the scaling theory of localization; 1.3.2 The main equations of one-parameter scaling; 1.3.3 Model solutions; 1.3.4 Some predictions of the scaling theory; 1.3.5 Minimum metallic conductivity; 1.4 EXTENDED-STATE CONDUCTION IN THREE DIMENSIONS 1.4.1 Activated conduction1.4.2 Extended-state conduction near the metal-insulator transition; 1.5 APPARENT MOBILITY EDGE AND EXTENDED-STATE CONDUCTION IN TWO-DIMENSIONAL SYSTEMS; 1.5.1 Experimental studies of the mobility edge in low-mobility two- dimensional systems; 1.5.2 Evidence for a true metal-insulator

transition in high-mobility two-dimensional systems; 1.5.3 Evidence against a true metal-insulator transition in two-dimensional systems; 1.5.4 Temperature-dependent charge carrier scattering; 1.6 CONCLUSIONS; REFERENCES; 2: Description of Charge Transport in Amorphous Semiconductors

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Sommario/riassunto

The field of charge conduction in disordered materials is a rapidly evolving area owing to current and potential applications of these materials in various electronic devices. This text aims to cover conduction in disordered solids from fundamental physical principles and theories, through practical material development with an emphasis on applications in all areas of electronic materials. International group of contributors Presents basic physical concepts developed in this field in recent years in a uniform manner Brings up-to-date, in a one-stop source, a key evolving area in